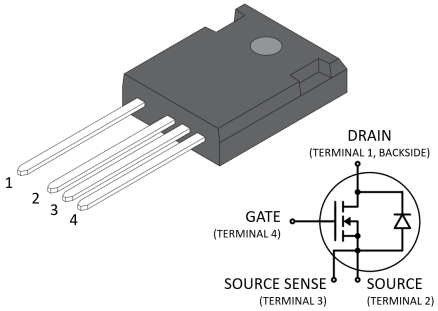
MSC750SMA170B4 Silicon Carbide N-Channel Power MOSFET

Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC750SMA170B4 device is a 1700 V, 750 mΩ SiC MOSFET in a TO-247 package with a source sense.



Features

The following are key features of the MSC750SMA170B4 device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)}$ = 175 °C
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

The following are benefits of the MSC750SMA170B4 device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

The MSC750SMA170B4 device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

Device Specifications

This section shows the specifications of the MSC750SMA170B4 device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC750SMA170B4 device.

Table 1 • Absolute Maximum Ratings

Symbol	Characteristic	Ratings	Unit
V_{DSS}	Drain source voltage	1700	V
I_D	Continuous drain current at T_C = 25 °C	7	A
	Continuous drain current at T_C = 100 °C	5	
I_{DM}	Pulsed drain current[1]	12	
V_{GS}	Gate-source voltage	23 to –10	V
P_D	Total power dissipation at T_C = 25 °C	68	W
	Linear derating factor	0.46	W/°C

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC750SMA170B4 device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		1.46	2.19	°C/W
T_J	Operating junction temperature	–55		175	°C
T_{STG}	Storage temperature	–55		150	
T_L	Soldering temperature for 10 seconds (1.6 mm from case)			260	
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m
Wt	Package weight		0.22		oz
			6.2		g

Electrical Performance

The following table shows the static characteristics of the MSC750SMA170B4 device. T_J = 25 °C unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)\ DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 100 µA	1700			V
$R_{DS(on)}$	Drain-source on resistance[1]	V_{GS} = 20 V, I_D = 2.5 A		750	940	mΩ
$V_{GS(th)}$	Gate-source threshold voltage	V_{GS} = V_{DS}, I_D = 100 µA	1.8	3.25		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	V_{GS} = V_{DS}, I_D = 100 µA		–5.7		mV/°C
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1700 V, V_{GS} = 0 V			100	µA
		V_{DS} = 1700 V, V_{GS} = 0 V T_J = 125 °C			500	
I_{GSS}	Gate-source leakage current	V_{GS} = 20 V/–10 V			±100	nA

Note:

1. Pulse test: pulse width < 380 µs, duty cycle < 2%.

The following table shows the dynamic characteristics of the MSC750SMA170B4 device. T_J = 25 °C unless otherwise specified.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DD} = 1360 V V_{AC} = 25 mV, ƒ = 1 MHz		184		pF
C_{rss}	Reverse transfer capacitance			2		
C_{oss}	Output capacitance			14		
Q_g	Total gate charge	V_{GS} = –5 V/20 V, V_{DD} = 1200 V I_D = 2.5 A		11		nC
Q_{gs}	Gate-source charge			2.9		
Q_{gd}	Gate-drain charge			2.1		
$t_{d(on)}$	Turn-on delay time	V_{DD} = 1200 V, V_{GS} = –5 V/20 V I_D = 5 A, $R_{G(ext)}$ = 8 Ω, Freewheeling diode = MSC750SMA170B4 (V_{GS} = –5 V)		13		ns
t_f	Voltage fall time			12		
$t_{d(off)}$	Turn-off delay time			7		

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_r	Voltage rise time			8		
E_{on}	Turn-on switching energy			107		µJ
E_{off}	Turn-off switching energy			17		
$t_{d(on)}$	Turn-on delay time	V_{DD} = 1200 V, V_{GS} = –5 V/20 V I_D = 5 A, $R_{G(ext)}$ = 8 Ω, T_J = 150 °C Freewheeling diode = MSC750SMA170B4 (V_{GS} = –5 V)		13		ns
t_f	Voltage fall time			12		
$t_{d(off)}$	Turn-off delay time			7		
t_r	Voltage rise time			8		
E_{on}	Turn-on switching energy			185		µJ
E_{off}	Turn-off switching energy			20		
ESR	Equivalent series resistance	f = 1 MHz, 25 mV, drain short		2.89		Ω
SCWT	Short circuit withstand time	V_{DS} = 1200 V, V_{GS} = 20 V		2.5		µs
E_{AS}	Avalanche energy, single pulse	V_{DS} = 150 V, V_{GS} = 20 V, I_D = 2.5 A		360		mJ

The following table shows the body diode characteristics of the MSC750SMA170B4 device. T_J = 25 °C unless otherwise specified.

Table 5 • Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	I_{SD} = 2.5 A, V_{GS} = 0 V		3.8		V
		I_{SD} = 2.5 A, V_{GS} = –5 V		3.9		V
t_{rr}	Reverse recovery time	I_{SD} = 5 A, V_{GS} = –5 V, V_{DD} = 1200 V, dI/dt = –2000 A/µs Drive Rg = 8 Ω		18		ns
Q_{rr}	Reverse recovery charge			120		nC
I_{RRM}	Reverse recovery current			3.0		A

Typical Performance Curves

This section shows the typical performance curves of the MSC750SMA170B4 device.

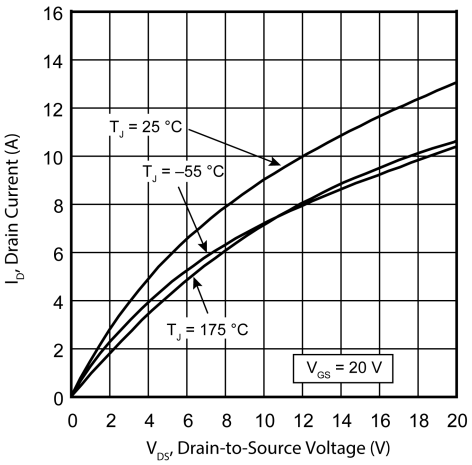


Figure 1 • Drain Current vs. V_{DS}

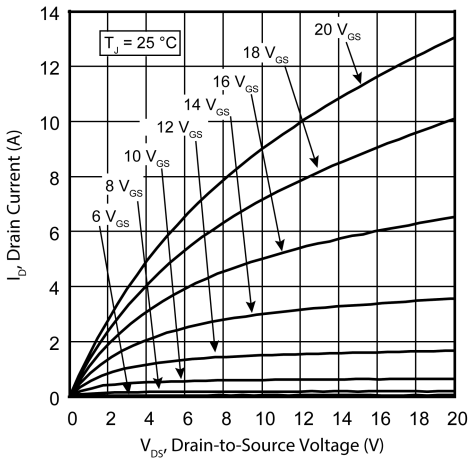


Figure 2 • Drain Current vs. V_{DS}

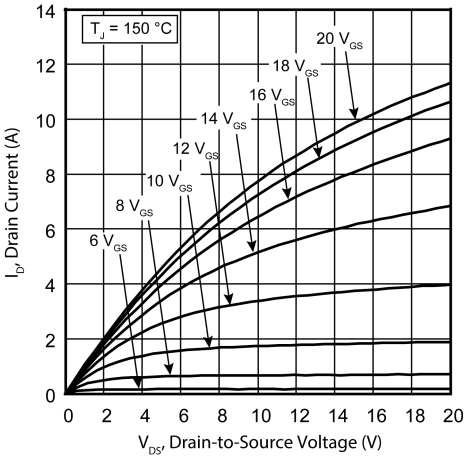


Figure 3 • Drain Current vs. V_{DS}

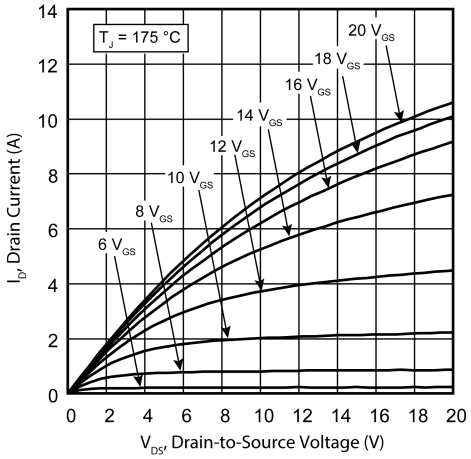


Figure 4 • Drain Current vs. V_{DS}

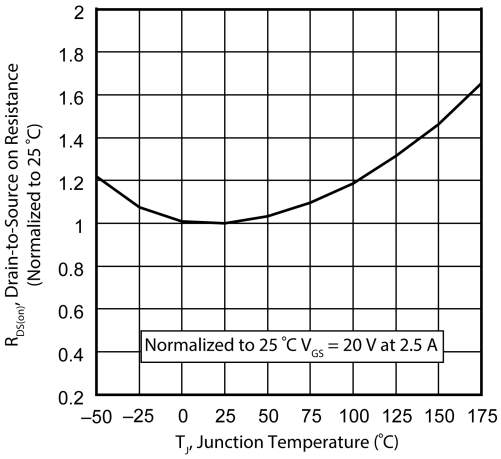


Figure 5 • RDS(on) vs. Junction Temperature

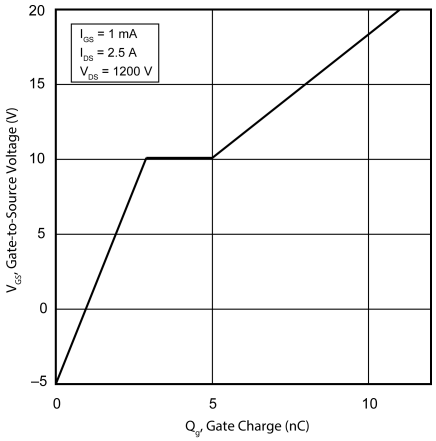


Figure 6 • Gate Charge Characteristics

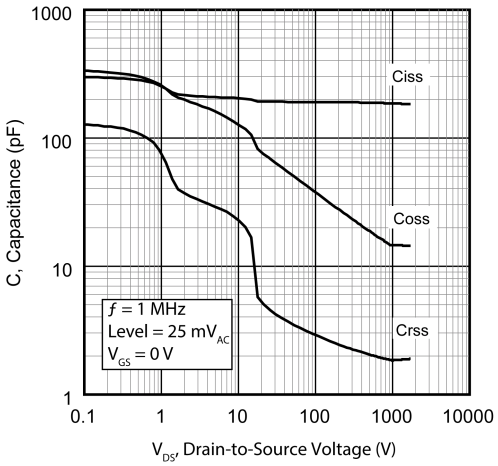


Figure 7 • Capacitance vs. Drain-to-Source Voltage

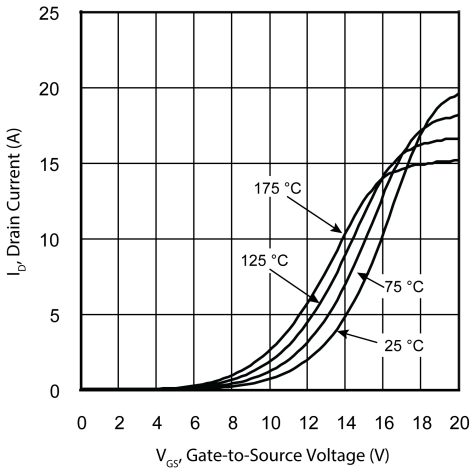


Figure 8 • I_D vs. Gate-to-Source Voltage

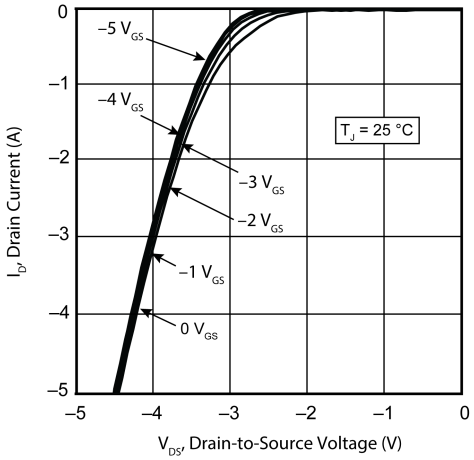


Figure 9 • I_D vs. V_{DS} 3rd Quadrant Conduction

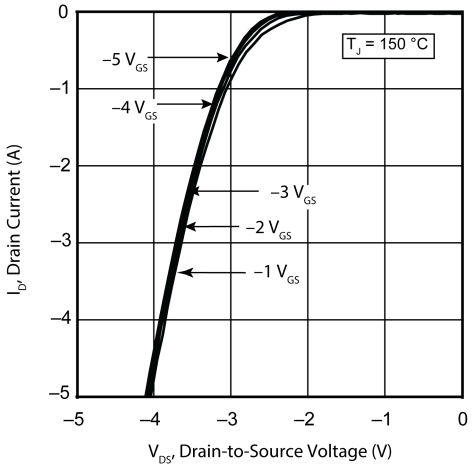


Figure 10 • I_D vs. V_{DS} 3rd Quadrant Conduction

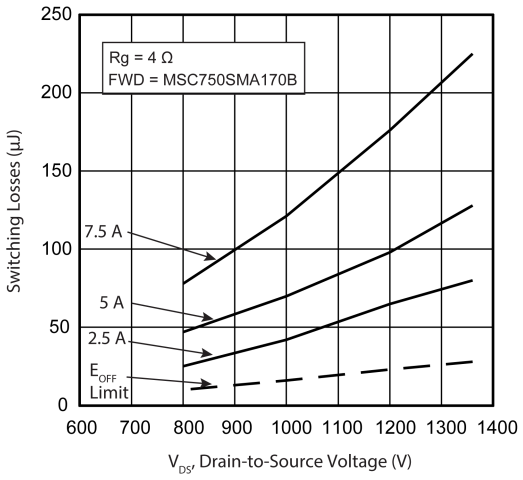


Figure 11 • Switching Energy vs. V_{DS} & I_D

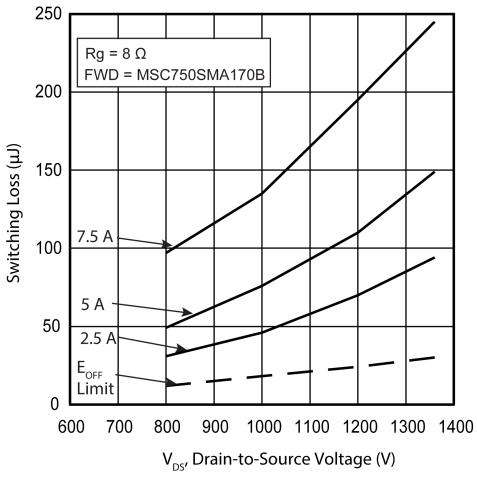


Figure 12 • Switching Energy vs. V_{DS} & I_D

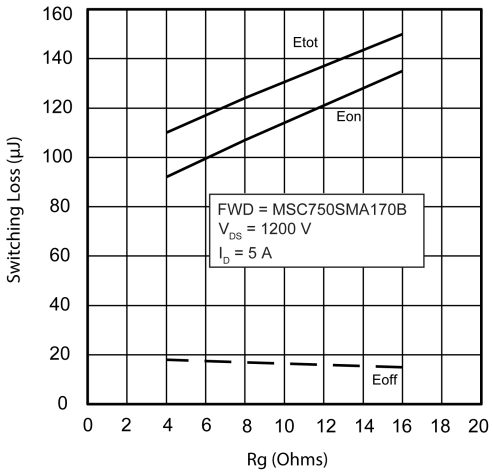


Figure 13 • Switching Energy vs. Rg

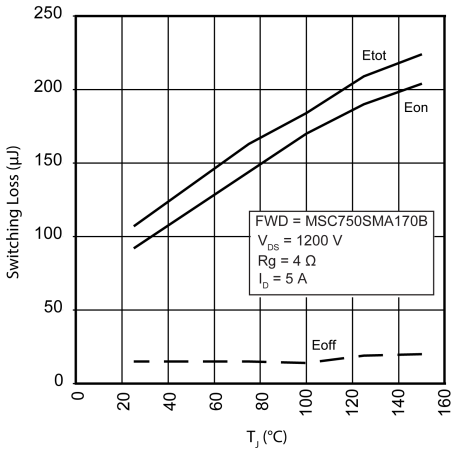


Figure 14 • Switching Energy vs. Temperature

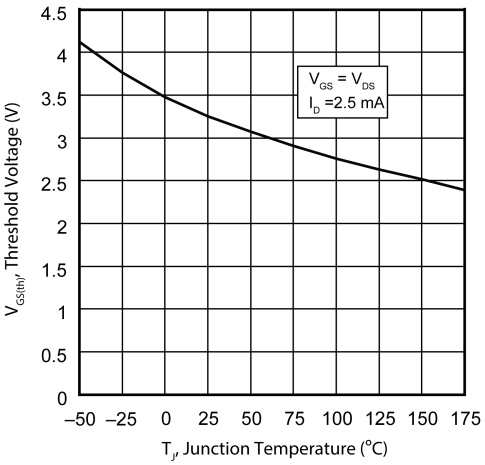


Figure 15 • Threshold Voltage vs. Junction Temp.

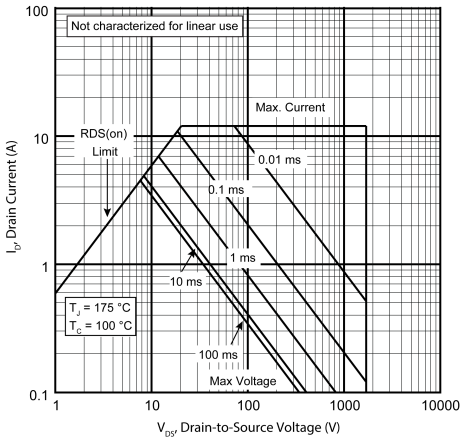


Figure 16 • Forward Safe Operating Area

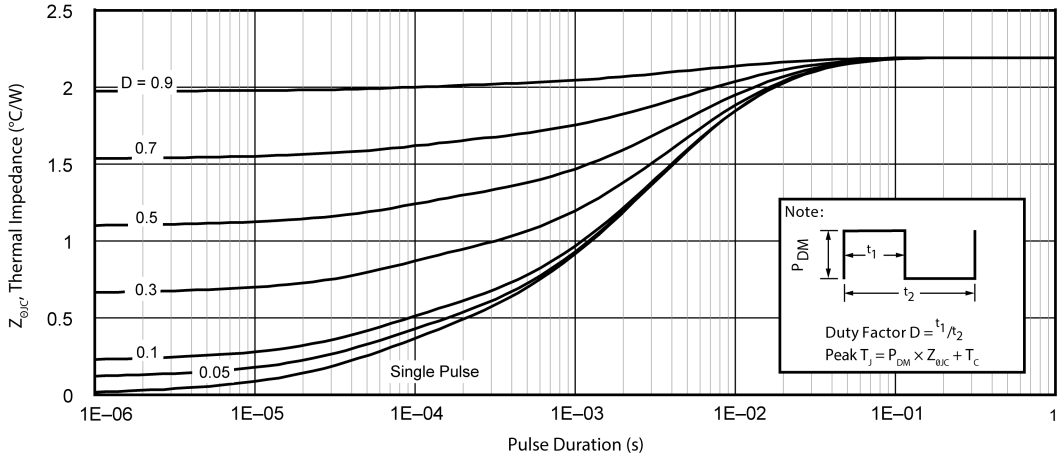


Figure 17 • Maximum Transient Thermal Impedance

Package Specification

This section shows the package specification of the MSC750SMA170B4 device.

Package Outline Drawing

The following figure illustrates the TO-247 4-lead package outline of the MSC750SMA170B4 device.

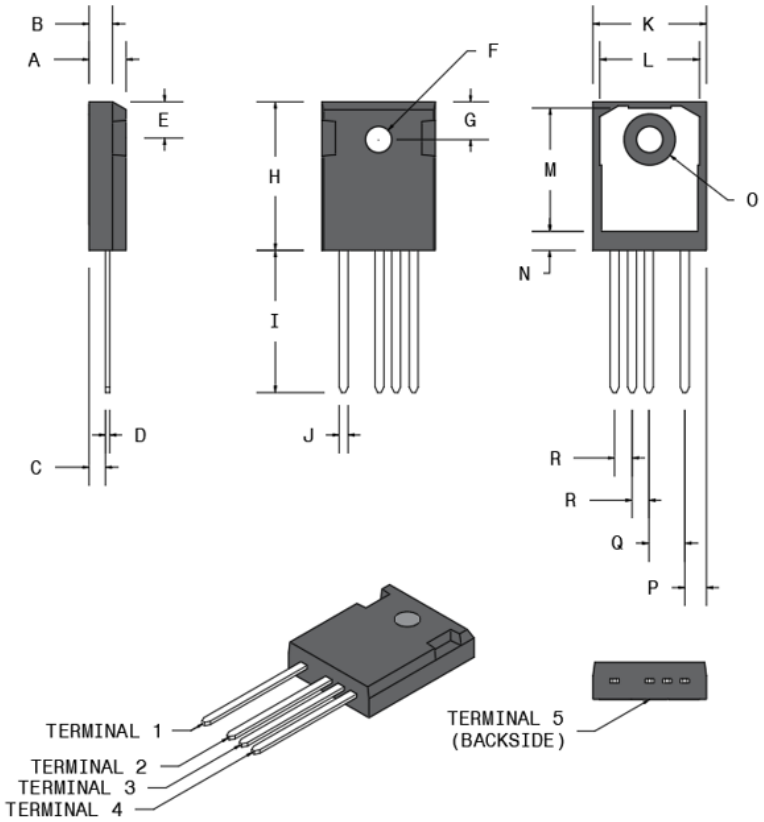


Figure 18 • Package Outline Drawing

The following table shows the TO-247 4-lead dimensions and should be used in conjunction with the package outline drawing.

Table 6 • TO-247-4L Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.90	5.17	0.193	0.204
B	1.85	2.11	0.073	0.083
C	2.25	2.51	0.089	0.099
D	0.55	0.68	0.022	0.027
E	5.49	5.74	0.216	0.226

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
F	3.56	3.66	0.140	0.144
G	6.15 BSC		0.242 BSC	
H	20.83	21.08	0.820	0.830
I	19.81	20.32	0.780	0.800
J	1.07	1.33	0.042	0.052
K	15.77	16.03	0.621	0.631
L	13.89	14.15	0.547	0.557
M	16.25	16.85	0.640	0.663
N	2.00	2.75	0.079	0.108
O	7.10	7.50	0.280	0.295
P	2.87 BSC		0.113 BSC	
Q	5.08 BSC		0.200 BSC	
R	2.54 BSC		0.100 BSC	
Terminal 1	Drain			
Terminal 2	Source			
Terminal 3	Source sense			
Terminal 4	Gate			
Terminal 5	Drain			

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